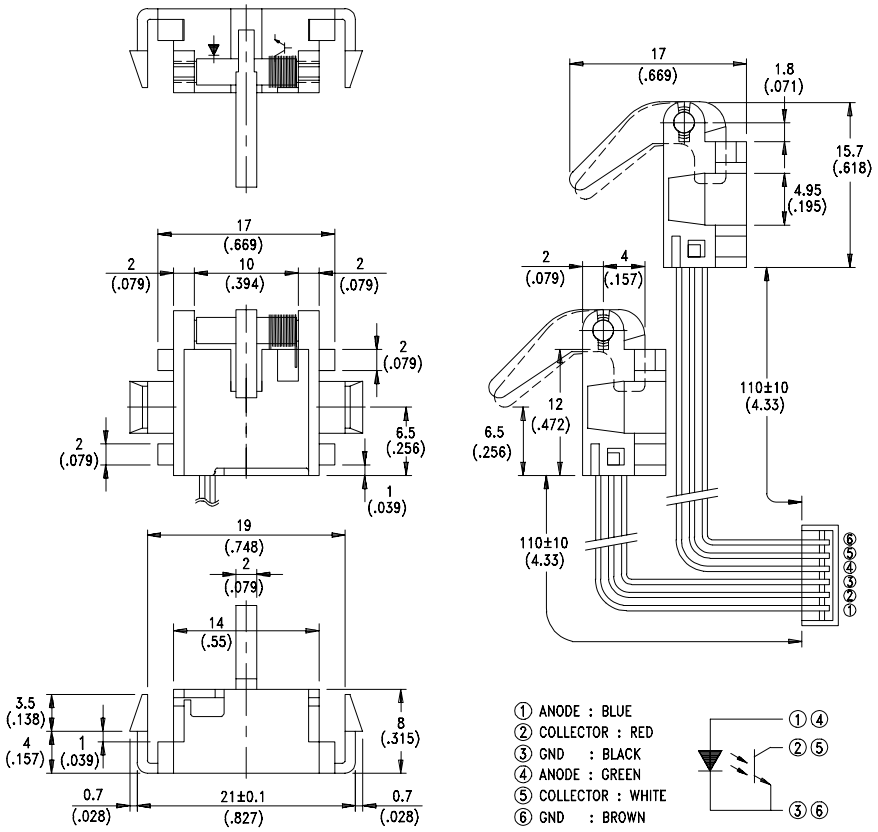
FEATURES

* SNAP MOUNTING.
* MECHANICAL SWITCH REPLACEMENT.
* THREE WIRES FOR ELECTRICAL CONNECTION.
* CUSTOMIZED LEVER ARM CAN BE DESIGNED FOR SPECIFIC APPLICATION.

PACKAGE DIMENSIONS



NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25mm(.010") unless otherwise noted.
3. Specifications are subject to change without notice.

ABSOLUTE MAXIMUM RATINGS AT TA=25℃

PARAMETER	MAXIMUM RATING	UNIT
IR Diode Continuous Forward Current	50	mA
IR Diode Reverse Voltage	5	V
Transistor Collector Currant	20	mA
Transistor Power Dissipation	75	mW
IR Diode Peak Forward Current (Pulse Wide = 10 μS, 300 pps)	1	A
Diode Power Dissipation	60	mW
Phototransistor Collector-Emitter Voltage	30	V
Phototransistor Emitter-Collector Voltage	5	V
Operating Temperature Range	-25℃ to + 85℃	
Storage Temperature Range	-55℃ to + 100℃	
Lead Soldering Temperature [1.6mm (.063“) Form Case]	260℃ for 5 Seconds	

ELECTRICAL OPTICAL CHARACTERISTICS AT TA=25℃

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
INPUT LED						
Forward Voltage	VF		1.2	1.6	V	I_F = 20mA
Reverse Current	IR			100	μA	VR=5V
OUTPUT PHOTOTRANSISTOR						
Collector-Emitter Breakdown Voltage	$V(BR)_{CEO}$	30			V	IC=1mA
Emitter-Collector Breakdown Voltage	$V(BR)_{ECO}$	5			V	IE=100 μA
Collector-Emitter Dark Current	ICEO			100	nA	VCE=10V
COUPLER						
Collector-Emitter Saturation Voltage	VCE(SAT)			0.4	V	IC=0.2mA IF=20mA
On State Collector Current	Ic(ON)	0.5	2		mA	VCE=5V IF=20mA

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25℃ Ambient Temperature Unless Otherwise Noted)

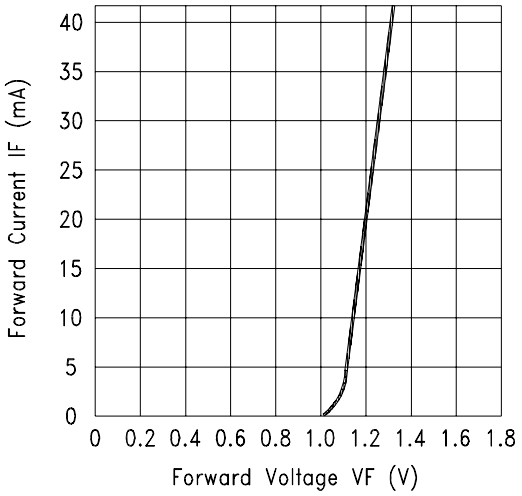


Fig.1 FORWARD CURRENT VS. FORWARD VOLTAGE

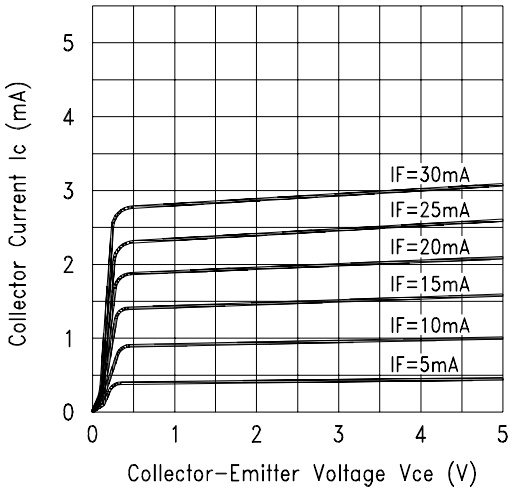


Fig.2 COLLECTOR CURRENT VS. COLLECTOR VOLTAGE

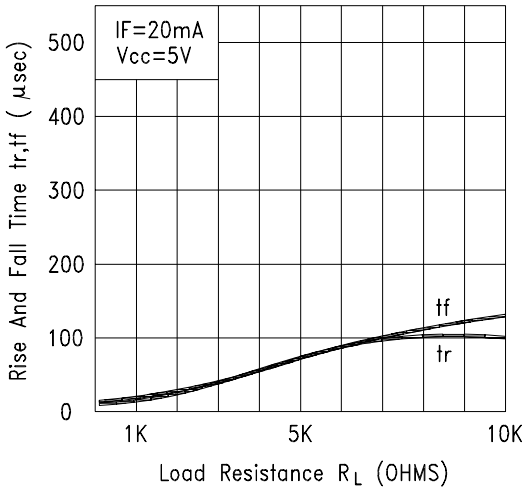


Fig.3 RISE AND FALL TIME VS. LOAD RESISTANCE

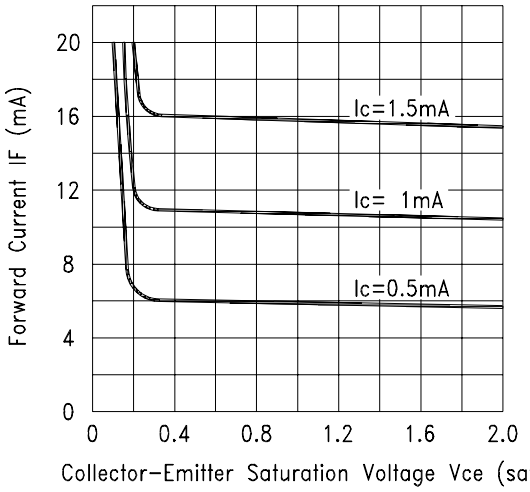


Fig.4 FORWARD CURRENT VS. Collector-Emitter Saturation Voltage